

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Chen, *et al.* Docket No.: TSM6283131RI
Serial No: 10/650,886 Art Unit: 1763
Date Filed: August 28, 2003 Examiner: George A. Goudreau
Title: In-Situ Strip Process for Polysilicon Etching in Deep Sub-Micron Technology

RECEIVED
CENTRAL FAX CENTER
JUN 08 2006

Mail Stop Amendment
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

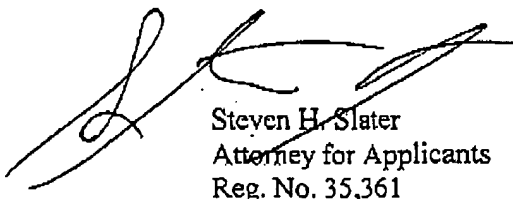
Applicants wish to bring to the attention of the U.S. Patent and Trademark Office the information noted on the enclosed PTO Form PTO/SB/08A, which may be considered material to the examination of the above-identified application.

This Information Disclosure Statement is submitted under 37 C.F.R. §1.97(c) together with a \$180.00 fee under 37 C.F.R. §1.17(p) after the C.F.R. §1.97(b) time period, but before final action or notice of allowance, whichever occurs first.

Please charge the required fee of \$180.00 and any additional amount, or credit any overpayment to Deposit Acct. No 50-1065 of the below mentioned firm.

06/09/2006 CNGUYEN2 00000031 501065 10650886
01 FC:1806 180.00 DA

Respectfully submitted,



Steven H. Slater
Attorney for Applicants
Reg. No. 35,361

Slater & Matsil, L.L.P.
17950 Preston Road, Suite 1000
Dallas, Texas 75252
Tel: (972) 732-1001
Fax: (972) 732-9218

